ATLAS ITk Strip Detector for High-Luminosity LHC

刘佩莲 (IHEP) n behalf of the ATLAS ITL Chinese Gr

On behalf of the ATLAS ITk Chinese Group

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Roadmap to High Luminosity LHC

- HL-LHC (2029): $\mathcal{L} \sim 7.5 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$
 - To provide 300 fb⁻¹/year during an operating period of \sim 10 years
 - Up to 200 inelastic *pp* interactions per beam crossing (pileup)
 - Increased luminosity \rightarrow ~10 times higher radiation





Harsh environment

Phase-II Upgrade of ATLAS Detector for HL-LHC

- All-silicon new Inner Tracker (ITk) → Main upgrade
- New inner barrel trigger chambers
- New readout electronics for all systems
- New High-Granularity Timing Detector (2.4 < $|\eta|$ < 4.0)
 - Proposed to distinguish between collisions



Upgrade of the ATLAS Inner Detector



- New all-silicon Inner Tracker (ITk)
- Finer granularity: 10xstrip channels ; 60xpixel channels
- Extended coverage to η of 4 ($|\eta| < 2.5$ for present tracker)
- Reduced material budget



ATLAS ITk Strip



1.4 m

IHEP contributes to the strip <u>barrel</u> detector

Barrel: 4 layers (double sided)

- L3/L2 with **long strip** (LS) modules
- L1/L0 with **short strip** (SS) modules
- Up to \sim 33MRad dose and 7.2 × 10¹⁴n_{eq}/cm²

4 barrel layers Stave LS wafer 4.83 cm strips 2.41 cm strips

1.4 m

ITk main element: Modules

- Consists of one sensor, one/two hybrids, and one power board
 - Hybrids and power boards are glued directly to silicon sensor







ITk Strip Sensors

- n^+ -in-p with p-stop isolation
 - Collects electrons -> faster signal, reduced charge trapping
 - Always depletes from the segmented side -> good signal even not fully depleted
 - Active area 9.7×9.7 cm², strip pitch 75.5 μ m
 - Produced by Hamamatsu Photonics K.K. (HPK) in 6-inch, 320 μm thick wafers





Bias Voltage [V]

- Halfmoons to validate the characteristics and performance of the sensors
 - Mini sensors, Monitor diodes, test structure ...
- Operation bias voltage is set to backplane at -500V at $-30^{\circ}C$

ITk Strip Sensors – Study of radiation effects

- Radiation tolerant (1. $6 \times 10^{15} n_{eq}/cm^2$)
- Mini sensors with same layout as main barrel sensors but with 8mm of strip length.
- Proton irradiation at China Spallation Neutron Source (CSNS)
 - 3x10⁹ protons/cm²/s @80MeV

T = +20C

600

Reverse Bias [V]

500

400

Sensor characterization

Current<100µA@500V

– I-V, C-V

T = -20C

200

100

300

Current [uA]

10 =

10

10-2

10

10-4

Charge collection efficiency measurement









Hybrid and Powerboard

Hybrid

- 10 x ATLAS Binary Chip (ABCstar) : custom FE ASICs read 256 channels
- 1x Hybrid Controller Chip (HCCstar) : an aggregation readout chip as interface between ABCstars and stave

Powerboard

- **AMACstar**(Autonomous Monitoring And Control): monitors voltage/current/temp
- **DC-DC converter** transforms 11V supply to 1.5V for ASICs





All connections are made by Al wire-bonds

HCCstar

ASICs and TID Bump

- All 3 ASICs made in 130nm CMOS technology at Global Foundries (GF)
- TID bump: a well known feature of 130nm GF chips
- Surface effects: generation of charge traps due to ionizing energy loss (Total Ionising Dose, TID)
- Leakage current was induced by positive charge trapped in the bulk of the shallow trench isolation (STI)
 - The creation/trapping of charge (by radiation, faster)
 - Its passivation/de-trapping (by thermal excitation, slower)







GF 130nm ASICs TID Bump Solution

Big challenge on power and cooling. How to Mitigate?

IBL readout chip FE-I4 (130nm)

•

Insertable B Layer (innermost pixel layer) installed @2014



0.5

Dose (Mrad)

Dose [Mrad]

ASICs and Single Event Effects

- Single Event Effects (SEE): change of state in memory/logic due to an electrical disturbance from radiation, resulting in wrong data and misconfiguration
- Mitigation of Single Event Effects
 - Triplication logic and flip-flops as well as reset and clock trees
 - Voting system

• Irradiation test of ABCstar and HCCstar

 $- 3x10^9 \text{ protons/cm}^2/\text{s}$ @80MeV at CSNS



Send 0/1s to chips and read them back (configuration registers and physics package)



Data	flow	SEE :	$\mathcal{O}(10^{-}$	¹⁰)errors/event/chip
noise	occu	ipancy	: $\mathcal{O}(10^{-1})$	⁻²)errors/event/chip

Chip Type	Institute	$\sigma_{\rm SEU}[cm^2/p]$
VO	IHEP	$(6.3\pm0.08)\times10^{-12}$
vo	TRUME	$(3.7\pm0.03)\times10^{-12}$
V1	IKIOWI	$(7.4\pm0.08)\times10^{-12}$

Hybrid and Module Quality Control @IHEP



10 cycling between -40°C and +40°C, 12 hours

Local Support Structure: Stave Core

- Mechanical support using high stiffness and high thermal conductively carbon fiber
- Embedded Ti cooling pipes with evaporative CO2 $(-40^{\circ}C)$
- Copper on Polyimide (Kapton) bus tapes routing electrical connections from and to modules





Staves

- 28 Barrel modules on each stave (14 modules per side)
 - Modules are rotated wrt the beam line by \pm 26 mrad to provide stereo information
- Readout and control electronics
 - **ABCstar**: FE chips communicate with HCCstar on each hybrid
 - HCCstar: send data at 640Mbps and receive clock and commands at 160Mbps from the End of Substructure (EoS) board over bus tapes
 - EoS board: fibre optic driver/receiver (VTRx+) and low power GigaBit Transceiver (IpGBT, 65nm CMOS CERN developed ASIC)



Strip Barrel Integration

- **Staves will be inserted in four concentric Carbon cylinders**
 - 392 barrel staves in total
 - Pre-dressed with stave locking brackets
- The global structure, Outer Cylinder (**OC**), hosts the ITk
- The barrel integration will be performed at CERN









Strip System Test

- System Test validates production chain with final parts and cooling before production starts
 - Powering chain, cooling, readout...
 - Parallel readout of multiple staves at 1MHz
 - Tests with CO2 cooling system
- Barrel system test is populated with 8 staves (5 LS + 3 SS)



Cold Noise delayed Module production by a year

- Unfortunately in May 2022 before modules enter production, a technical issue was discovered
 - Cold Noise appear below -20° C , only in strip channels under PB and hybrids
 - Dedicated studies tracked down to capacitors in the DCDC domain of the powerboard vibrating at 2MHz
 - **Piezoelectric effect** below -20° C
 - Vibrations travelling across the sensor and coupling back into the sensors
 - By May 2023 a mitigation technique was put in place: changing the glue which minimizes the noise (different stiffness)
- Module production was delayed by a year



Project status – Sensor Cracks

- Another technical challenge discovered in June 2023 during stave tests
- Some sensors failed high voltage testing (early breakdown <100V)
- Cracks appear at some point during thermal cycling/powering (R.T. to -40°C) only on some modules
- Simulations indicate the issue is the coefficient thermal expansion (CTE) mismatch between bybrids/powerboard and sensor
 - Stress peaks between hybrids and powerboard
- Mitigation
 - 'Interposer' added between the flexes and sensor
 - 95% of stress reduced















IHEP Site Module Production

- To deliver 1000 ITk Strip barrel modules and contribute to system integration/testing
- Passed all 29 Site Qualification steps for Module production
- Produced 8 prototype and 6 pre-production modules
 - Protoype 5LS + 3LS
 - PPA x 3 (1LS + 2SS) and PPB x 3 (3LS)



IHEP Site for ITk Strip Module



Summary

- In view of HL-LHC, the ATLAS experiment will upgrade its complete Inner Detector with an all silicon Inner Tracker (ITk)
- ITk is expected to improve the ATLAS performance operating under a harsh environment
- The **Strip detector** has been through many years of design and R&D with the **pre-production** 'smoothly' ongoing in several areas
- Two major technical issues have significantly delayed the production schedule
 - **Cold Noise** issue has been mitigated by changing the glues
 - Sensor Crack issue is still under investigation
- The production will start soon.

backup

Alibava System

- ALiBaVa (A Liverpool Barcelona Valencia collaboration) system is an analogue readout system used to read out the signal from the sensors
- Two different laboratory setups
 - Radioactive source setup
 - Laser setup
- Detector board
 - 1 or 2 sensors
- Daughter board
 - 2 Beetle chips
 - 128 channels each
 - Analogue or binary output mode
 - HV power supply for sensors
 - Sending analogue output signals to the motherboard



Beam Test



Main goal is to demonstrate pre-production module performance

- ✓ To check uniformity of response across various sensor regions
- ✓ To evaluate track reconstruction capability
- ✓ To determine operational window: eff.>99% and noise occu.<0.1%



Staves

- 28 Barrel modules on each stave (14 modules per side)
 - Modules are rotated wrt the beam line by \pm 26 mrad to provide stereo information
- The End of Substructure (EoS) electronic board
 - Facilities the communication and power distribution for all modules
 - Hosts radiation-hard fibre transmitter receiver
 (VTRx+) and associated electrical transceivers
 (IpGBT, low power GigaBit Transceiver





Staves: Temperature Measurement





- AMACStar allows on-stave temperature monitoring using the 10K NTCs on hybrids and power boards - HX, HY and PB NTCs
- Affected by module-module variation
- Module temperatures linear with stave temperature

System Integration



Module Assembly and Metrology @IHEP

- Amount and height of glue matters
 - Heat emission, mechanical support, wire bonding
 - Controlled by glue robot and tooling







• Metrology for position and tilt, and glue height



• Pull test to measure the strength of bonded wires







powerboard



AMACStar

GaNFET

Allows the isolation of a failed sensor in breakdown connected to the same HV line using commercial GaNFET switch Enables/Disable DCDC

 Measure Voltage, Currents and Temperatures

bPOL12V

- Radiation hard buck converter
- 11V input, 1.5V output
- Air-core coil

LinPOL12V

- Radiation hard linear regulator
- 11V input
- 1.4V output for AMACStar
- 3.3V output for HV switch enable



Module Assembly



Align Sensor on sensor plate



Dispense glue on Hybrid through Stencil
 Glue Hybrids on sensor





• Module without Powerboard



• Glue Powerboard to sensor



Assembled Module



Type Invertion

n-type silicon after high fluences: (type inverted)



p-type silicon after high fluences: (still p-type)



- + p-in-n (LHC)
 - Collects holes (slower)
 - Depleted from the back
- n-in-p (HL-LHC)
 - Collects electrons
 - High CCE even not fully depleted